Title (en)

Semiconductor component and method of manufacture

Title (de)

Halbleiter-Bauelement und Herstellungsverfahren

Title (fr)

Composant semi-conducteur et méthode de fabrication

Publication

EP 1351286 A3 20050112 (EN)

Application

EP 03007073 A 20030327

Priority

US 11478402 A 20020401

Abstract (en)

[origin: EP1351286A2] A semiconductor component includes a semiconductor substrate (310) having a first conductivity type, a first semiconductor device (320) at least in a first portion of the semiconductor substrate, and a second semiconductor device (330, 340) at least in a second portion of the semiconductor substrate. The first semiconductor device includes a first electrode region (321), a second electrode region (322), a body region (323), and an isolation region (324) in the first portion of the semiconductor substrate. The body region has the first conductivity type, and the first electrode region, the second electrode region, and the isolation region have a second conductivity type. The second electrode region has a different doping concentration than the first electrode region, and the body region is isolated from the second portion of the semiconductor substrate by the isolation region and the first electrode region. <IMAGE>

IPC 1-7

H01L 21/761; H01L 27/088; H01L 21/8234; H01L 29/78; H01L 29/08

IPC 8 full level

H01L 21/761 (2006.01); **H01L 21/762** (2006.01); **H01L 29/78** (2006.01); H01L 29/08 (2006.01)

CPC (source: EP US)

H01L 21/761 (2013.01 - EP US); **H01L 21/762** (2013.01 - EP US); **H01L 29/7801** (2013.01 - US); **H01L 29/7816** (2013.01 - EP US); H01L 29/0653 (2013.01 - EP); H01L 29/0847 (2013.01 - US); H01L 29/0886 (2013.01 - EP)

Citation (search report)

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- [Y] EP 0146181 A2 19850626 - PHILIPS NV [NL]
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Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IT LI LU MC NL PT RO SE SI SK TR

DOCDB simple family (publication)

EP 1351286 A2 20031008; **EP 1351286 A3 20050112**; **EP 1351286 B1 20080116**; DE 60318643 D1 20080306; DE 60318643 T2 20080605; US 2003183899 A1 20031002; US 6747332 B2 20040608

DOCDB simple family (application)

EP 03007073 A 20030327; DE 60318643 T 20030327; US 11478402 A 20020401